#### Етапи та календарний план виконання проєкту учасника конкурсу

#### **Project Title**

Development of physical base of both acoustically controlled modification and machine learningoriented characterization for silicon solar cells

#### Scientific head of the project

Olikh Oleg Yaroslavovych, doctor of science (physics and mathematics), associate professor

- 4. The project implementation stages and schedule of the tender participant
- 4.1. The project implementation stage (PIS) and performance indicators

**PIS** № 1: <u>15.09.2020 -30.09.2020</u>

PIS Title: The project's material and computation base formation. PIS Objectives: The preparation for calculations and measurements.

Task 1. The development of a calculation model of silicon  $n^+$ -p- $p^+$  structure for using in solar cell simulation program SCAPS 3.3.08; the model must take into account real values and temperature dependences of parameters for silicon and traps from modern literature; development of software for auto-creation model with various parameters.

Task 2. The selection of silicon solar cells (SSCs) with a boron doped base and a high iron impurity concentration.

The performance indicators:

the software for auto-creation model of  $n^+$ -p- $p^+$  structure for solar cell simulation program SCAPS 3.3.08; set of SSC with various doping degree.

### **PIS** № 2: 01.10.2020-15.12.2020

PIS Title: The numerical simulation of current-voltage characteristics of  $n^+$ -p- $p^+$  structure.

PIS Objectives: To calculate an data array of IVC of  $n^+-p-p^+$  structure with various parameters, to test a technique for measuring the kinetics of light-induced processes in SSC.

Task 1. The development of software for parsing of SCAPS result file; the calculation of IVC for silicon  $n^+$ -p- $p^+$  structures with different base thickness (150-240 µm), base doping level (10<sup>15</sup>-10<sup>17</sup> cm<sup>-3</sup>), impurity concentration (10<sup>10</sup>-10<sup>13</sup> cm<sup>-3</sup>) over the temperature range 290-340 K.

Task 2. The testing f procedure for measuring the kinetics of light-induced processes in SSC.

Task 3. The preparation of a presentation for an international conference.

Task 4. The equipment purchase.

The performance indicators:

the data array of calculated IVC for silicon  $n^+$ -p- $p^+$  structures with various geometric and electrophysical characteristics; the software for parsing of SCAPS result file; a prepared presentation; test results of measuring of kinetics of light-induced processes in SSC; prepared documentation for the equipment purchase.

#### **PIS** № 3 : 01.01.2021 -31.03.2021

PIS Title: The development of procedure for estimation of IVC kinetic parameters under ultrasound loading conditions.

PIS Objectives: to implement procedure for estimation of kinetic parameter of defect rebuilding in barrier structures under ultrasound loading conditions; to fit IVC data array accordingly to the two-diode model.

- Task 1. The development of procedure for estimation of kinetic parameter of defect rebuilding in barrier structures under ultrasound loading conditions. Testing measurements.
- Task 2. The determination of influence of light-induced Fe-B pair dissociation on the IVC parameters (an ideality factor, a saturation current, a shunt resistance, an open-circuit voltage, a short-circuit current) of silicon solar cells; the quantification of kinetic of IVC parameters change induced by Fe-B pair association.
- Task 3. The software implementation of the meta-heuristic optimization method Jaya; determination of ideality factor value for the calculated IVC array according to the two-diode model.
  - Task 4. The preparation of a presentation for an international conference.
  - Task 5. The equipment purchase.

## The performance indicators:

the setup of for estimation of kinetic parameter of defect rebuilding in barrier structures under ultrasound loading conditions; the quantification of influence of light-induced Fe-B pair dissociation on the IVC parameters; the software for Jaya implementation; the data array of ideality factor value for silicon  $n^+$ -p- $p^+$  structures with various geometric and electrophysical characteristics; a prepared presentation; prepared documentation for the equipment purchase.

## **PIS** № 4 : 01.04.2021 -30.06.2021

PIS Title: Making of an artificial neural network for estimating the concentration of iron in SSC.

PIS Objectives: to find out the physical regularities of acousto-defective interaction in SSC under longitudinal ultrasound loading; to make an artificial neural network for estimation of impurity iron atom concentration by IVC parameters.

- Task 1. The determination of regularities of SSC parameters change, which forced by light-induced degradation, under longitudinal ultrasonic loading condition.
- Task 2. The determination of kinetic characteristics of IVC parameters variation due to Fe-B pair association under longitudinal ultrasonic loading condition
- Task 3. The tinning of hyperparameters of an artificial neural network capable of predicting the impurity iron atom concentration by ideality factor value; neural network training.
  - Task 4. The preparation of a presentation for an international conference.

#### The performance indicators:

the recognized physical regularities of interaction of defect complexes, which associated with transition metal atoms, and longitudinal elastic waves; the tuned an artificial neural network for estimating the concentration of iron in  $n^+$ -p- $p^+$  structures; a prepared presentation;

#### **PIS** № 5 : 01.07.2021 -30.09.2021

PIS Title: The transverse ultrasonic waves as a tool for SSC parameter driving.

PIS Objectives: to find out the physical regularities of interaction of defect complexes, which associated with transition metal atoms, and transverse ultrasonic waves in SSC.

- Task 1. The determination of regularities of SSC parameters change, which forced by light-induced degradation, under transverse ultrasonic loading condition.
- Task 2. The determination of kinetic characteristics of IVC parameters variation due to Fe-B pair association under transverse ultrasonic loading condition
  - Task 3. The paper preparation.

#### The performance indicators:

the recognized physical regularities of interaction of defect complexes, which associated with transition metal atoms, and longitudinal elastic waves; a prepared paper.

#### **PIS** № 6 : 01.10.2021 -15.12.2021

PIS Title: The specification of physical mechanisms of acousto-defective interaction and development of recommendations for practical use.

PIS Objectives: to summarize of the project obtained results in the recommendations.

- Task 1. The determination of the physical mechanisms of the influence of acoustic waves on the rebuilding of defect complexes, which associated with transition metal atoms, in SSC.
- Task 2. The development of recommendations about practical using of ultrasound loading during SSC manufacturing.
- Task 3. The development of recommendations for the method of quantitative evaluation of electrically active defects in barrier structures by the ideality factor value
  - Task 4. The paper preparation.

#### The performance indicators:

the explored physical mechanisms of the interaction between defect complexes, which associated with transition metal atoms, in SSC and ultrasonic waves; the recommendation both for the practical use of ultrasound loading in SSC manufacturing and for the quantitative evaluation of electrically active defects in barrier structures by the ideality factor value; a prepared paper

# 4.2. Project implementation schedule (by quarters)

	Implementation period						
Project implementation stage and tasks	Year 1		Year 2				
	3 quarter	4 quarter	1 quarter	2 quarter	3 quarter	4 quarter	
1. The project's material and computation base formation	+						
Task 1. The development of a calculation model of silicon $n^+$ - $p$ - $p^+$ structure for using in solar cell simulation program SCAPS 3.3.08; the model must take into account real values and temperature dependences of parameters for silicon and traps from modern literature; development of software for autocreation model with various parameters	+						
Task 2. The selection of silicon solar cells (SSCs) with a boron doped base and a high iron impurity concentration.	+						
Funding amount, thousand uah	72,3						
2. The numerical simulation of current-voltage characteristics of $n^+$ - $p$ - $p^+$ structure		+					
Task 1. The development of software for parsing of SCAPS result file; the calculation of IVC for silicon $n^+$ - $p$ - $p^+$ structures with different base thickness (150-240 µm), base doping level (10 <sup>15</sup> -10 <sup>17</sup> cm <sup>-3</sup> ), impurity concentration (10 <sup>10</sup> -10 <sup>13</sup> cm <sup>-3</sup> ) over the temperature range 290-340 K		+					
Task 2. The testing f procedure		+					

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for measuring the kinetics of light-induced processes in SSC					
Task 3. The preparation of a presentation for an international conference		+			
Task 4. The equipment purchase.					
Funding amount, thousand uah		2947,6			
3. The development of procedure for estimation of IVC kinetic parameters under ultrasound loading conditions			+		
Task 1. The development of procedure for estimation of kinetic parameter of defect rebuilding in barrier structures under ultrasound loading conditions. Testing measurements			+		
Task 2. The determination of influence of light-induced Fe-B pair dissociation on the IVC parameters (an ideality factor, a saturation current, a shunt resistance, an open-circuit voltage, a short-circuit current) of silicon solar cells; the quantification of kinetic of IVC parameters change induced by Fe-B pair association			+		
Task 3. The software implementation of the metaheuristic optimization method Jaya; determination of ideality factor value for the calculated IVC array according to the two-diode model			+		
Task 4. The preparation of a presentation for an international conference			+		

Task 5. The equipment purchase					
Funding amount, thousand uah		1772,8			
4. Making of an artificial neural network for estimating the concentration of iron in SSC			+		
Task 1. The determination of regularities of SSC parameters change, which forced by light-induced degradation, under longitudinal ultrasonic loading condition			+		
Task 2. The determination of kinetic characteristics of IVC parameters variation due to Fe-B pair association under longitudinal ultrasonic loading condition			+		
Task 3. The tinning of hyperparameters of an artificial neural network capable of predicting the impurity iron atom concentration by ideality factor value; neural network training			+		
Task 4. The preparation of a presentation for an international conference			+		
Funding amount, thousand uah			617,5		
5. The transverse ultrasonic waves as a tool for SSC parameter driving				+	
Task 1. The determination of regularities of SSC parameters change, which forced by light-induced degradation, under transverse ultrasonic loading condition				+	

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Task 2. The determination of kinetic characteristics of IVC parameters variation due to Fe-B			+	
pair association under transverse ultrasonic loading condition				
Task 3. The paper preparation			+	
Funding amount, thousand uah			606,4	
(The specification of physical				
6. The specification of physical mechanisms of acousto-defective interaction and development of recommendations for practical use				+
Task 1. The determination of the physical mechanisms of the influence of acoustic waves on the rebuilding of defect complexes, which associated with transition metal atoms, in SSC				+
Task 2. The development of recommendations about practical using of ultrasound loading during SSC manufacturing				+
Task 3. The development of recommendations for the method of quantitative evaluation of electrically active defects in barrier structures by the ideality factor value				+
Task 4. The paper preparation				+
Funding amount, thousand uah				492,2